line 13, delete "differently" insert --are different--;

line 16, delete "includes" insert --has an--.

Claim 3, line 1, delete "semic onductor" insert --semiconductor--;

line 4, delete "with" insert --having an--;

line 5, delete "that are".

Claim 4, line 5, delete "with" insert --having an--;

line 6, delete "that are".

Claim 5, line 5, delete "with" insert --which has an--;

line 6, after "type" insert --of--;

line 7, after "group" insert --consisting--.

Claim 6, line 4, after "type" insert --of--.

Claim 7, line 4, after "type" insert --of--.

Claim 8, line 3, delete "with" insert --having--;

line 5, delete "by" insert --in--.

A'

9. (amended) A semiconductor device in accordance with claim 1, wherein

an oxide composing said [doubl e] double-layered conductive oxide layer consists of at least one type of compound selected from a group consisting of $CaRuO_3$, $SrRuO_3$, and $SrTiO_3$ to which La is added by over 0.5 weight % to 4.0 weight% (included), and all of [them having the] which have a perovskite structure.

A1 Cont'd.

10. (amended) A [semicond uctor] semiconductor device in accordance with claim 1, wherein

an oxide composing said double-layered conductive oxide layer has a mixed phase of at least one type of compound selected from a group consisting of $CaRuO_3$, $SrRuO_3$, and $SrTiO_3$ which La is added by over 0.5 weight% to 4.0 weight% (included), and all of [them having the] which have a perovskite structure, with an [alkalline] alkaline-earth metal oxide composing said compound, that is, CaO or SrO.

Claim 11, line 3, delete "with sai d" insert --having said--;

line 5, delete "by" insert --in--.

Claim 13, line 3, delete "conduct I've" insert --conductive--; same line 3, delete "with" insert --having--;

line 4, delete "said"; same line 4, delete "by" insert --in--;

line 7, delete "ReO $_3$" insert --ReO_3--.

Claim 14, line 3, delete "with" insert --having--.

A2

17. (amended) A method for manufacturing a semiconductor device, including a process for forming a conductive oxide layer [with] having an oxygen deficiency, [by] comprising the steps of sputtering or evaporating elements composing said conductive oxide in a non-oxidizing atmosphere, and then forming a conductive oxide layer on said conductive oxide

A² cont'd. layer [with] having said oxygen deficiency, thereby forming a lower electrode layer on a substrate; a process for forming an oxide dielectric layer on said lower electrode layer; and a process for forming an upper electrode layer on said oxide dielectric layer, wherein

said lower electrode layer consists mainly of two conductive oxide layers formed in the same crystal structure and consisting of the same element, but different from each other in oxygen composition ratio, and

said lower and upper electrode layers, as well as said oxide dielectric layer, are combined thereby composing an oxide dielectric capacitor.

Claim 18, line 1, delete "for" insert --of--.

Claim 19, line 1, delete "for" insert --of--.

Claim 20, line 1, delete "for" insert --of--;

line 3, delete "with" insert --having--;

line 5, delete "the" insert --a--;

line 6, delete "the" insert --a--;

line 7, after "is" insert --in--.

A³ 21. (amended) A method [for] of manufacturing a semiconductor device in accordance with claim 17, wherein

said conductive oxide layer [with] having said oxygen deficiency, which is formed in said double-layered conductive oxide layer, is then formed with [the] a sputtering method or

A3 Concld.

[the] a vacuum deposition method, and said non-oxidizing atmospheric gas consists of at least one type of gas selected from oxygen [(O_2)] (O_2), nitric monoxide [(N_2O)] (N_2O), nitric dioxide (NO_2), and ozone (O_3), and the pressure or partial pressure of said gas is 10 μTorr or below.

Claim 22, line 9, after "layer" insert --,--.

Claim 23, line 1, delete "devic e" insert --device--.

Claim 26, line 3, after "type" insert --of--;

line 4, after "group" insert --consisting--.

Claim 27, line 3, after "type" insert --of--;

line 4, delete "of IrO_2" and insert --consisting of IrO_3--.

Claim 28, line 1, delete "accor dance" and insert --accordance--;

line 4, delete "$Ti_{1-x}Al_x)_{1-}$" insert --$(Ti_{1-x}Al_x)_{1-y}N_y$--;

line 5, delete "$_yN_y$".

Claim 29, line 1, delete "accordanc e" insert --accordance--.

A4

31. (amended) A method [for] of manufacturing a semiconductor device, [including;] comprising:

a step [for] of forming a lower electrode layer including an aluminum titanium nitride layer on a substrate by sputtering in a nitridizing atmosphere;

A1 cont'd

a step [for] of forming an oxide dielectric layer on said lower electrode layer; and

a step [for] of forming an upper electrode layer on said oxide dielectric layer, wherein

both lower and upper electrode layers, as well as said oxide dielectric layer, are combined thereby composing an oxide dielectric capacitor.

Claim 32, line 1, delete "for" insert --of--.

Claim 33, line 1, delete "for" insert --of--;

line 4, delete "preventing" insert --prevents--;

line 5, after "oxidation" insert --and--.

Claim 34, line 1, delete "for" insert --of--;

line 4, delete "preventing" insert --to prevent--.

A5

35. (amended) A semiconductor device, including[;]:

a first area consisting of a semiconductor material; a second area connected to said first area and consisting of [said] a first conductive material; a third area connected to said second area and consisting of [said] a second conductive material; a fourth area connected to said third area and consisting of an oxide dielectric material; and a fifth area connected to said fourth area and consisting of a conductive material, wherein

As Concld.)

the material composition at the interface of said first area adjacent to said second area is approximately equal to the average material composition of said first area, and the material compositions at the interface of said second area adjacent to said first area, as well as to said third area, is approximately equal to the average material composition of said second area.

36. (amended) A semiconductor device, including[;]:

a first area [consi sting] consisting of a conductive semiconductor material; a second area connected to said first area and consisting of [said] a first conductive material; a third area connected to [said] a second area and consisting of said second conductive material; a fourth area connected to said third area and consisting of an oxide dielectric material; and a fifth area connected to said fourth area and consisting of a conductive material, wherein

the average resistivity of said first area is approximately equal to the resistivity of said semiconductor material and the average resistivity of said second area is approximately equal to the resistivity of said first conductive material.

IN THE ABSTRACT OF THE DISCLOSURE:

Delete line 2, and insert --A--;

line 3, delete "for" insert --of--; same line 3, delete "that";

line 4, after "and" insert --is able--;

line 5, after "of" (first occurrence) insert --a--;

line 7, after "11," insert --an--; same line 7, delete "dielectrics" insert --dielectric layer--;

line 11, delete "These" insert --The--;

line 12, delete "in" insert --to have--; same line 12, delete "with" insert --are of--;

line 14, delete "includes" insert --has an--;

line 15, delete "including" insert --which has an--;

line 17, after "interface" insert --,--;

line 18, delete "oxidation" insert --oxidizing--.

REMARKS

The specification has been amended to correct errors of a typographical and grammatical nature. Due to the excessive corrections thereto, applicants submit herewith a Substitute Specification, along with a marked-up copy of the original specification for the Examiner's convenience. Applicants submit that the substitute specification includes the changes as shown in the marked-up copy and includes no new matter. Therefore, entry of the Substitute Specification is respectfully requested.